

L Number	Hits	Search Text	DB	Time stamp
1	2	((("6456640") or ("6118800")).PN.	USPAT; US-PGPUB	2004/08/05 11:46
2	0	(nitride or nitrogen) and bandgap and saturable near3 absor\$8 and 372/11.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 11:54
3	0	(nitride or nitrogen) and bandgap and saturable near3 absor\$8 and 372/25.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 11:54
4	9	bandgap and saturable near3 absor\$8 and 372/11.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 11:56
5	11	bandgap and saturable near3 absor\$8 and 372/25.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 12:00
6	7	bandgap and saturable near3 absor\$8 and 372/26.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 12:32
7	1	bandgap and saturable near3 absor\$8 and 372/30.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 12:33
8	2	bandgap and saturable near3 absor\$8 and 372/39.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 12:34
9	7	bandgap and saturable near3 absor\$8 and 372/43.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 13:28
10	0	("9408437").PN.	USPAT; US-PGPUB	2004/08/05 13:23
11	0	"09408437"	USPAT; US-PGPUB	2004/08/05 13:23
12	1	"09/408437"	USPAT; US-PGPUB	2004/08/05 13:23
13	40	bandgap and saturable near3 absor\$8 and 372/45.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 15:31
14	38	bandgap and saturable near3 absor\$8 and 372/46.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 15:33
15	13	(bandgap and saturable near3 absor\$8 and 372/46.ccls.) not (bandgap and saturable near3 absor\$8 and 372/45.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 15:31
16	29	bandgap and saturable near3 absor\$8 and 372/50.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 16:49
17	1	bandgap and saturable near3 absor\$8 and 372/29.02.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 16:49

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1	2	((("6456640") or ("6118800"))).PN.	USPAT; US-PGPUB	2004/08/05 11:46
2	0	(nitride or nitrogen) and bandgap and saturable near3 absor\$8 and 372/11.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 11:54
3	0	(nitride or nitrogen) and bandgap and saturable near3 absor\$8 and 372/25.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 11:54
4	9	bandgap and saturable near3 absor\$8 and 372/11.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 11:56
5	11	bandgap and saturable near3 absor\$8 and 372/25.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 12:00
6	7	bandgap and saturable near3 absor\$8 and 372/26.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 12:32
7	1	bandgap and saturable near3 absor\$8 and 372/30.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 12:33
8	2	bandgap and saturable near3 absor\$8 and 372/39.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 12:34
9	7	bandgap and saturable near3 absor\$8 and 372/43.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 13:28
10	0	("9408437").PN.	USPAT; US-PGPUB	2004/08/05 13:23
11	0	"09408437"	USPAT; US-PGPUB	2004/08/05 13:23
12	1	"09/408437"	USPAT; US-PGPUB	2004/08/05 13:23
13	40	bandgap and saturable near3 absor\$8 and 372/45.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 15:31
14	38	bandgap and saturable near3 absor\$8 and 372/46.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 15:33
15	13	(bandgap and saturable near3 absor\$8 and 372/46.ccls.) not (bandgap and saturable near3 absor\$8 and 372/45.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 15:31
16	29	bandgap and saturable near3 absor\$8 and 372/50.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 15:33
-	458	bandgap and semiconductor and (absorb\$3 near layer)	USPAT; US-PGPUB	2003/08/25 08:55
-	100	(bandgap and semiconductor and (absorb\$3 near layer)) and 372/\$.ccls.	USPAT; US-PGPUB	2003/03/22 15:51
-	18	bandgap and semiconductor and ((saturable adj absorb\$3) near layer)	USPAT; US-PGPUB	2003/03/22 16:04
-	4	bandgap and semiconductor and (absorb\$3 near layer) and (self near oscillat\$3) and (self near pulsat\$3)	USPAT; US-PGPUB	2003/03/22 16:22
-	14	bandgap and semiconductor and (absorb\$3 near layer) and (saturable near absorb\$3) and (self near pulsat\$3)	USPAT; US-PGPUB	2003/03/22 16:23

-	6	bandgap and semiconductor and (light near absorb\$3 near layer) and (saturable near absorb\$3) and (self near pulsat\$3)	USPAT; US-PGPUB	2003/03/22 16:37
-	6	bandgap and (light adj absorb\$3 near layer) and (saturable adj absorb\$3) and (self near pulsat\$3)	USPAT; US-PGPUB	2003/03/22 16:50
-	3	bandgap and (saturable adj absorb\$3) and (self near pulsat\$3) and nitrogen	USPAT; US-PGPUB	2003/03/22 16:51
-	3	bandgap and (saturable adj absorb\$3) and (self near pulsat\$3) and nitride	USPAT; US-PGPUB	2003/03/22 17:34
-	11	bandgap and (saturable adj absorb\$3) and (nitride or nitrogen)	USPAT; US-PGPUB	2003/03/22 17:37
-	19	bandgap and (saturable adj absorb\$3) and (self near pulsat\$3)	USPAT; US-PGPUB	2003/03/22 17:44
-	19	((saturable adj absorb\$3) and (self near pulsat\$3) and (nitrogen or nitride or "N")) and bandgap	USPAT; US-PGPUB	2003/03/22 17:45
-	50	(saturable adj absorb\$3) and (self near pulsat\$3) and (nitrogen or nitride or "N")	USPAT; US-PGPUB	2003/03/22 17:48
-	51	(saturable adj absorb\$4) and (self near pulsat\$3) and (nitrogen or nitride or "N")	USPAT; US-PGPUB	2003/03/22 17:50
-	58	(saturable adj absorb\$5) and (self near pulsat\$3) and (nitrogen or nitride or "N")	USPAT; US-PGPUB	2003/03/22 17:57
-	18	(saturable adj absorb\$5) and (self near pulsat\$3) and (nitrogen or nitride)	USPAT; US-PGPUB	2003/03/22 18:23
-	6	(saturable adj absorb\$5) and (self near pulsat\$3) and (nitrogen or nitride) and bandgap	USPAT; US-PGPUB	2003/03/23 17:18
-	22	(saturable adj absorb\$5) and (self near pulsat\$3) and bandgap	USPAT; US-PGPUB	2003/03/22 18:29
-	18	(saturable adj absorb\$5) and (self near pulsat\$3) and (nitrogen or nitride)	USPAT; US-PGPUB	2003/03/23 17:59
-	6	(saturable adj absorb\$5) and (self near pulsat\$3) and (nitrogen)	USPAT; US-PGPUB	2003/03/23 17:33
-	0	(saturable adj absorb\$5) near "AlGaInPN"	USPAT; US-PGPUB	2003/03/23 17:34
-	0	(saturable adj absorb\$5) near "AlGalnasN"	USPAT; US-PGPUB	2003/03/23 17:34
-	0	(saturable adj absorb\$5) near "GalnasN"	USPAT; US-PGPUB	2003/03/23 17:34
-	3	(saturable adj absorb\$5) and (group near "V") and (mix\$3 near crystal)	USPAT; US-PGPUB	2003/03/23 17:38
-	17	(saturable adj absorb\$5) and "ingan"	USPAT; US-PGPUB	2003/03/23 17:38
-	3	(saturable adj absorb\$5) and "inganp"	USPAT; US-PGPUB	2003/03/23 17:39
-	3	(saturable adj absorb\$5) and "inganas"	USPAT; US-PGPUB	2003/03/23 17:40
-	1	(saturable adj absorb\$5) and "ingansb"	USPAT; US-PGPUB	2003/03/23 17:40
-	0	(saturable adj absorb\$5) and "inganbi"	USPAT; US-PGPUB	2003/03/23 17:41
-	17	(saturable adj absorb\$5) and (self near pulsat\$3) and (nitride)	USPAT; US-PGPUB	2003/03/23 18:09
-	46	(saturable adj absorb\$3) and (nitride)	USPAT; US-PGPUB	2003/03/23 18:10
-	368	(absorb\$4 near layer\$1) and (group near "V")	USPAT; US-PGPUB	2003/07/01 14:45
-	208	((absorb\$4 near layer\$1) and (group near "V")) and nitrogen	USPAT; US-PGPUB	2003/07/01 13:07
-	204	((absorb\$4 near layer\$1) and (group near "V")) and nitrogen) and As	USPAT; US-PGPUB	2003/07/01 13:07
-	4	((absorb\$4 near layer\$1) and (group near "V")) and nitrogen) and saturable	USPAT; US-PGPUB	2003/07/01 13:26
-	0	(saturable near absorb\$5) and algainnp	USPAT; US-PGPUB	2003/07/01 13:34
-	69	(saturable near absorb\$5) and nitrogen	USPAT; US-PGPUB	2003/07/01 14:36
-	5	((saturable near absorb\$5) and nitrogen) and group near "III-V"	USPAT; US-PGPUB	2003/07/01 13:28
-	6	algainnp	USPAT; US-PGPUB	2003/07/01 14:39

-	0	((absorb\$4 near layer\$1) and (group near "V")) and algainnp	USPAT;	2003/07/01 14:36
-	86	(saturable same absorb\$5) and nitrogen	US-PGPUB USPAT;	2003/07/01 14:41
-	79	(saturable with absorb\$5) and nitrogen	US-PGPUB USPAT;	2003/07/01 14:37
-	4	((absorb\$4 near layer\$1) and (group near "V")) and ((saturable with absorb\$5) and nitrogen)	US-PGPUB USPAT;	2003/07/01 14:37
-	4	((absorb\$4 near layer\$1) and (group near "V")) and ((saturable same absorb\$5) and nitrogen)	US-PGPUB USPAT;	2003/07/01 14:39
-	0	algainnp and ((saturable same absorb\$5) and nitrogen)	US-PGPUB USPAT;	2003/07/01 14:39
-	0	algainnp and ((saturable with absorb\$5) and nitrogen)	US-PGPUB USPAT;	2003/07/01 14:39
-	10	algainnas	US-PGPUB USPAT;	2003/07/01 14:40
-	2	algainnsb	US-PGPUB USPAT;	2003/07/01 14:39
-	0	algainnbi	US-PGPUB USPAT;	2003/07/01 14:39
-	12	algainnas	US-PGPUB USPAT;	2003/07/01 14:40
-	9	algainnp	US-PGPUB; EPO; JPO; DERWENT USPAT;	2003/07/01 14:40
-	2	algainnsb	US-PGPUB; EPO; JPO; DERWENT USPAT;	2003/07/01 14:40
-	0	algainnbi	US-PGPUB; EPO; JPO; DERWENT USPAT;	2003/07/01 14:40
-	1536	(saturable same absorb\$5)	US-PGPUB; EPO; JPO; DERWENT USPAT;	2003/07/01 14:46
-	1288	(saturable near absorb\$5)	US-PGPUB; EPO; JPO; DERWENT USPAT;	2003/07/01 14:41
-	1449	(saturable with absorb\$5)	US-PGPUB; EPO; JPO; DERWENT USPAT;	2003/07/01 14:42
-	0	algainnas and ((saturable same absorb\$5))	US-PGPUB; EPO; JPO; DERWENT USPAT;	2003/07/01 14:42
-	0	algainnas and ((saturable near absorb\$5))	US-PGPUB; EPO; JPO; DERWENT USPAT;	2003/07/01 14:42
-	0	algainnas and ((saturable with absorb\$5))	US-PGPUB; EPO; JPO; DERWENT USPAT;	2003/07/01 14:42
-	36281	absorb\$5 near layer\$1	US-PGPUB; EPO; JPO; DERWENT USPAT;	2003/07/01 14:46
-	154906	absorb\$5 same layer\$1	US-PGPUB; EPO; JPO; DERWENT USPAT;	2003/07/01 14:46

-	117840	absorb\$5 with layer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 14:46
-	148	((saturable same absorb\$5)) and (absorb\$5 near layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 14:51
-	461	((saturable same absorb\$5)) and (absorb\$5 same layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 14:47
-	404	((saturable same absorb\$5)) and (absorb\$5 with layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 14:47
-	390	((saturable near absorb\$5)) and (absorb\$5 same layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 14:47
-	339	((saturable near absorb\$5)) and (absorb\$5 with layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 14:48
-	144	((saturable with absorb\$5)) and (absorb\$5 near layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 14:48
-	447	((saturable with absorb\$5)) and (absorb\$5 same layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 14:48
-	393	((saturable with absorb\$5)) and (absorb\$5 with layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 14:48
-	117	((saturable near absorb\$5)) and (absorb\$5 near layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 14:48
-	0	algainnas and (absorb\$5 near layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 14:51
-	3	algainnp and (absorb\$5 with layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 14:52
-	0	algainnsb and (absorb\$5 near layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 14:52
-	2	algainnas and (absorb\$5 same layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 14:52
-	2	algainnas and (absorb\$5 with layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 14:55
-	0	algainnp and (absorb\$5 near layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 14:55
-	3	algainnp and (absorb\$5 same layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 14:55

-	1	algainnsb and (absorb\$5 same layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 14:59
-	1	algainnsb and (absorb\$5 with layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 15:08
-	1011	(nitride or nitrogen) near "V"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 15:37
-	35435	(nitride or nitrogen) same "V"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 15:38
-	285	((nitride or nitrogen) same "V") and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 15:38
-	11	((nitride or nitrogen) same "V") and 372/\$.ccls.) and ((self near pulsat\$5) or (self near oscillat\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 15:42
-	6043	((self near pulsat\$5) or (self near oscillat\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 15:43
-	1732	saturable near absor\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 15:45
-	145	((self near pulsat\$5) or (self near oscillat\$5))) and (saturable near absor\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 15:45
-	7	((self near pulsat\$5) or (self near oscillat\$5))) and (saturable near absor\$6)) and ((nitride or nitrogen) same "V")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/02 10:37
-	27	((self near pulsat\$5) or (self near oscillat\$5))) and (saturable near absor\$6)) and (nitride or nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/02 10:38
-	0	(saturable near3 absorb\$4 near3 (algainnp or gainnp))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/25 10:23
-	26	algainnp or gainnp	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/25 08:57
-	0	((saturable near3 absorb\$4) or (absorb\$4 near3 layer)) near3 (algainnp or gainnp))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/25 09:03
-	0	((saturable near3 absorb\$4) or (absorb\$4 near3 layer)) with (algainnp or gainnp))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/25 09:03
-	0	((saturable near3 absorb\$4) or (absorb\$4 near3 layer)) same (algainnp or gainnp))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/25 10:30
-	1	((saturable near3 absorb\$4) or (absorb\$4)) same (algainnp or gainnp))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/25 12:01

-	1	(saturable near3 absorb\$4 near3 (ternary or (multinary near3 alloys)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/25 10:24
-	586	((saturable near3 absorb\$4) or (absorb\$4)) same (ternary or (multinary near3 alloys)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/25 10:27
-	73	((saturable near3 absorb\$4) or (absorb\$4)) near3 (ternary or (multinary near3 alloys)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/25 10:27
-	16	((saturable near3 absorb\$4) or (absorb\$4 near3 layer)) near3 (ternary or (multinary near3 alloys)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/25 10:51
-	5	((saturable near3 absorb\$4) near3 (nitrogen))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/25 10:52
-	90	((saturable near3 absorb\$4) or (absorb\$4 near3 layer)) near3 (nitrogen))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/25 11:59
-	0	((saturable near3 absorb\$4) or (absorb\$6 near3 layer)) near3 (gainnp or algainnp))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/25 12:03
-	1	((saturable near3 absorb\$4) or (absorb\$6)) same (algainnp or gainnp))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/25 12:07
-	101	((saturable near3 absorb\$4) or (absorb\$6 near3 layer)) near3 (nitrogen))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 10:32
-	0	((self near3 pulsat\$3) near3 (algainnp or gainnp))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/25 12:10
-	0	((self near3 pulsat\$3) same (algainnp or gainnp))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/25 12:10
-	228	(saturable near3 absor\$7 near3 layer\$1) and (vcSEL or (semiconductor near3 laser))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 10:47
-	21	((saturable near3 absor\$7 near3 layer\$1) and (vcSEL or (semiconductor near3 laser))) and "III-V"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 10:34
-	6	((saturable near3 absor\$7 near3 layer\$1) and (vcSEL or (semiconductor near3 laser))) and "III-V" and (nitride\$1 or nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 14:24
-	1	(saturable near3 absor\$7 near3 layer\$1) near3 "III-V"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 10:48
-	0	(saturable near3 absor\$7 near3 layer\$1) near3 (inganp or ingansb or inganbi or ingann)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/05 11:42
-	1	(saturable near3 absor\$7 near3 layer\$1) near3 (ganas or ganp or inganas or gainnp)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 11:27

-	1	(saturable near3 absor\$7) near3 (ganas or ganp or inganas or gainnp)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 11:42
-	15	(saturable near3 absor\$7) and (active near3 (region or layer)) and (lattice near3 match\$3) and (nitrogen or nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 11:53
-	0	(saturable near3 absor\$7) and ((active near3 (region or layer)) near3 (lattice near3 match\$3)) and (nitrogen or nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 11:53
-	378	257/97.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 14:24
-	126	257/97.ccls. and (nitrogen or nitride or (gallium near3 nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 14:25
-	0	(257/97.ccls. and (nitrogen or nitride or (gallium near3 nitride))) and (saturable near3 absor\$8)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 14:26
-	53	(257/97.ccls. and (nitrogen or nitride or (gallium near3 nitride))) and (absor\$8)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 14:27
-	28	(257/97.ccls. and (nitrogen or nitride or (gallium near3 nitride))) and (absor\$8 near3 layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 14:41
-	0	257/97.ccls. and (saturable near absor\$8)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 14:42
-	1	257/103.ccls. and (saturable near absor\$8)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 14:42
-	0	257/97.ccls. and (saturable near3 absor\$8)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 14:42
-	1	257/103.ccls. and (saturable near3 absor\$8)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 14:46
-	31	257/\$5.ccls. and (saturable near3 absor\$8)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/26 14:47
-	12	(257/\$5.ccls. and (saturable near3 absor\$8)) and (nitrogen or nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/27 15:24
-	0	((self near3 pulsat\$3) near3 (algainp)) and cladding and (saturable near3 absor\$7 near3 nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/27 15:00
-	0	(cladding near3 (algainp)) and (saturable near3 absor\$7 near5 nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/27 15:01
-	308	(cladding near3 (algainp))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/27 15:01

-	29	((cladding near3 (algainp))) and self near3 pulsat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/27 15:01
-	209629	((cladding near3 (algainp))) and self near3 pulsat\$3) and nitrogen or nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/27 15:02
-	5	((cladding near3 (algainp))) and self near3 pulsat\$3) and (nitrogen or nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/27 15:16
-	2	((cladding near3 (algainp))) and self near3 pulsat\$3) and (nitrogen or nitride)) and saturable	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/27 15:16
-	61	((cladding near3 (algainp))) and (nitrogen or nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/27 15:16
-	3	((cladding near3 (algainp))) and (nitrogen or nitride)) and saturable	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/27 15:21
-	125	((saturable near3 absor\$7 near3 layer\$1) near3 nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/27 15:25
-	0	((saturable near3 absor\$7 near3 layer\$1) near3 nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/27 15:23
-	0	((saturable near3 layer\$1) near3 nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/27 15:24
-	150	(saturable near3 absor\$8) and (nitrogen or nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/27 15:24
-	0	((saturable near3 absor\$8 near3 layer\$1) near3 nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/27 15:25
-	5	saturable near3 absor\$8 near3 nitrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/27 15:26
-	25	nitrogen and (band near gap) and saturable	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/27 15:27
-	0	saturable near3 absorber near3 nitrogen near3 (band adj gap)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/01 13:18
-	1066	saturable near3 absorber	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/01 13:18
-	63	(saturable near3 absorber) and nitrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/01 13:19
-	5	((saturable near3 absorber) and nitrogen) and band adj gap	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/01 13:21

-	92	nitrogen near3 (band adj gap)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/01 13:30
-	0	(nitrogen near3 (band adj gap)) and saturable adj absorber	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/01 13:30
-	0	(nitrogen near3 (band adj gap)) and saturable adj absorb\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/01 13:22
-	0	(nitrogen near3 (band adj gap)) and saturable adj absor\$7	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/01 13:23
-	9	(nitrogen near3 (band adj gap)) and absorb\$7 near3 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/01 13:23
-	6	nitrogen near3 (band adj gap) near3 adjust\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/01 13:28
-	92	(nitrogen near3 (band adj gap)) and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/01 13:30
-	10	(nitrogen near3 (band adj gap)) and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/01 13:30
-	10	(nitrogen near3 (band adj gap)) and 372/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/01 13:30
-	0	semiconductor near3 laser and (saturable near3 absor\$6 near5 nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/18 11:18
-	1	semiconductor near3 laser and ((saturable near3 absor\$6 near3 layer) same nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/18 11:20
-	21	semiconductor near3 laser and ((saturable near3 absor\$6 near3 layer) and nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/18 11:24
-	5	semiconductor near3 laser and ((saturable near3 absor\$6 near3 layer) and nitrogen) and bandgap	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/18 11:35
-	7	semiconductor near3 laser and ((saturable near3 absor\$6 near3 layer) near3 (nitrogen or InGaN))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/18 11:39
-	9	semiconductor near3 laser and ((saturable near3 absor\$6 near3 layer) near3 (nitrogen or InGaN or nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/18 11:41
-	21	semiconductor near3 laser and ((saturable near3 absor\$6 near3 layer) same (nitrogen or InGaN or nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/18 11:54
-	278	semiconductor near3 laser and ((absor\$6 near3 layer) same (nitrogen or InGaN or nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/18 12:11

-	9	(semiconductor near3 laser and ((absor\$6 near3 layer) same (nitrogen or InGaN or nitride))) and self near3 pulsat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/18 11:54
-	24	(semiconductor near3 laser and self near3 pulsat\$3) and nitrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/18 13:17
-	210	semiconductor near3 laser and self near3 pulsat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/18 13:11
-	104	(semiconductor near3 laser and self near3 pulsat\$3) and absor\$9 near3 layer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/18 13:17
-	1	("5751756").PN.	USPAT; US-PGPUB	2004/03/21 11:11
-	7609	((saturable near3 absor\$9) or (absor\$9 near3 layer\$1)) same (nitrogen or n))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 11:14
-	1462	((saturable near3 absor\$9) or (absor\$9 near3 layer\$1)) same (nitrogen or n)) and semiconductor near3 laser	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 11:14
-	7410	((saturable near3 absor\$9 near3 layer\$1) or (absor\$9 near3 layer\$1)) same (nitrogen or n))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 12:02
-	1361	((saturable near3 absor\$9 near3 layer\$1) or (absor\$9 near3 layer\$1)) same (nitrogen or n)) and semiconductor near3 laser	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 11:14
-	1298	((saturable near3 absor\$9 near3 layer\$1) or (absor\$9 near3 layer\$1)) same (nitrogen or n)) and semiconductor near3 laser) and (as or p or sb or bi))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 11:15
-	524	((saturable near3 absor\$9 near3 layer\$1) or (absor\$9 near3 layer\$1)) same (nitrogen or n)) and semiconductor near3 laser) and (as or p or sb or bi)) and 372/\$.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 11:16
-	69	((saturable near3 absor\$9 near3 layer\$1) or (absor\$9 near3 layer\$1)) same (nitrogen or n)) and semiconductor near3 laser) and (as or p or sb or bi)) and self near3 pulsat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 11:16
-	1	((saturable near3 absor\$9 near3 layer\$1) same (nitrogen or nitride)) and ((clad\$4 near3 layer) same algainp)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 12:04
-	6	((saturable near3 absor\$9 near3 layer\$1) and (nitrogen or nitride)) and ((clad\$4 near3 layer) same algainp)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 12:04